

**Amendments to the Specification:**

Please replace the paragraph beginning on page 7, line 24, with the following rewritten paragraph:

Whereas in the embodiment represented in FIG. 7, the whole of the sacrificial layer is removed after doping and before superficial etching of the surfaces 4 and 5, in a particular embodiment, after doping and before the superficial etching phase, the sacrificial layer 2 is only partially etched, leaving at least one spacer block 8 between the layer 3 forming the substrate and the useful layer 1, as represented in FIG. 2. As in the document U.S. Pat. No. 5,750,420, the superficial etching phase of the surfaces 4 and 5 then uses the spacer block 8 as a mask so as to form the stops 6 and 7 in the surfaces 4 and 5. At the same time, it increases the roughness of the doped free zones of the surfaces 4 and/or 5. In addition, after the spacer block 8 has been removed, an additional superficial etching phase of the surfaces 4 and 5 can be performed to increase the roughness of the doped surface of the stops 6 and/or 7 (as shown in Figure 9, wherein R denotes the roughness of the doped surfaces of stops 6 and 7). This enables formation of stops of larger size than the flat stops without increasing the risk of sticking. Control of partial etching of the sacrificial layer 2 forming the spacer block 8 is thus made easier. Control of the dimensions of the spacer block is less critical than in the case described in the document U.S. Pat. No. 5,750,420 as the surface is rough.